

Radiation	Type	Technology	Electrodes
Blue	Standard	InGaN/Al ₂ O ₃	Both on top side

	typ. dimensions in μm ($\pm 20 \mu\text{m}$)
	<u>typ. thickness</u> 90 (± 20) μm <u>front side metalization</u> Au-alloy, 0.5 μm <u>backside metalization</u> Al-alloy, 1.5 μm

Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)		I_F	30	mA
Peak forward current	($t_p \leq 50 \mu\text{s}$, $t_p/T = 1/2$)	I_{FM}	100	mA
Operating temperature range		T_{amb}	-40 to +85	$^\circ\text{C}$
Storage temperature range		T_{stg}	-40 to +100	$^\circ\text{C}$

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		3.3	3.5	V
Reverse voltage	$I_F = 10 \mu\text{A}$	V_R	5			V
Luminous intensity ¹	$I_F = 20 \text{ mA}$	I_V	50	60		mcd
Peak wavelength	$I_F = 20 \text{ mA}$	λ_P	450	460	470	nm
Dominant wavelength	$I_F = 20 \text{ mA}$	λ_D		463		nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		25		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		20		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	$I_V(\text{typ})$ [mcd]	$V_F(\text{typ})$ [V]	Quantity
ELC-460-34				

Packing: Chips on adhesive film with wire-bond side on top